

FDMS3008SDC

N-Channel Dual Cool™ PowerTrench® SyncFET™

30 V, 65 A, 2.6 mΩ

Features

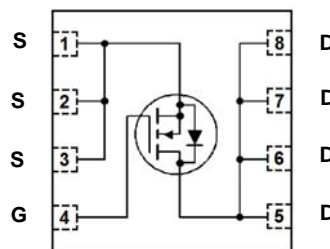
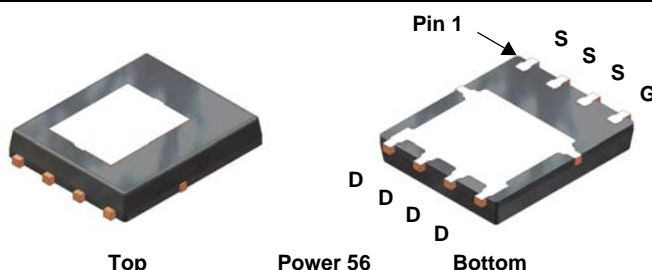
- Dual Cool™ Top Side Cooling PQFN package
- Max $r_{DS(on)}$ = 2.6 mΩ at $V_{GS} = 10$ V, $I_D = 28$ A
- Max $r_{DS(on)}$ = 3.3 mΩ at $V_{GS} = 4.5$ V, $I_D = 22$ A
- High performance technology for extremely low $r_{DS(on)}$
- SyncFET Schottky Body Diode
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process. Advancements in both silicon and Dual Cool™ package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Telecom Secondary Side Rectification
- High End Server/Workstation Vcore Low Side



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage (Note 4)	± 20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	65	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	140	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	29	
	-Pulsed	200	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	112	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 5)	2.3	V/ns
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	78	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	3.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	3.5	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	1.6	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	16	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	23	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	11	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
3008S	FDMS3008SDC	Dual Cool™ Power 56	13"	12 mm	3000 units



Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1\text{ mA}, V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, referenced to 25°C		13		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{ mA}$	1.2	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, referenced to 25°C		-5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 28\text{ A}$		1.8	2.6	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$		2.7	3.3	
		$V_{GS} = 10\text{ V}, I_D = 28\text{ A}, T_J = 125^\circ\text{C}$		2.4	3.6	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 28\text{ A}$		144		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		3400	4520	pF
C_{oss}	Output Capacitance			1115	1485	pF
C_{rss}	Reverse Transfer Capacitance			80	120	pF
R_g	Gate Resistance			0.7		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 28\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		15	27	ns
t_r	Rise Time			4.7	10	ns
$t_{d(off)}$	Turn-Off Delay Time			33	53	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 15\text{ V},$ $I_D = 28\text{ A}$	46	64	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$		21	29	nC
Q_{gs}	Gate to Source Charge			9.6		nC
Q_{gd}	Gate to Drain "Miller" Charge			4.3		nC

Drain-Source Diode Characteristics

V_{SD}	Source-Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2\text{ A}$ (Note 2)		0.4	0.8	V
		$V_{GS} = 0\text{ V}, I_S = 28\text{ A}$ (Note 2)		0.8	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 28\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		32	51	ns
Q_{rr}	Reverse Recovery Charge			39	62	nC

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

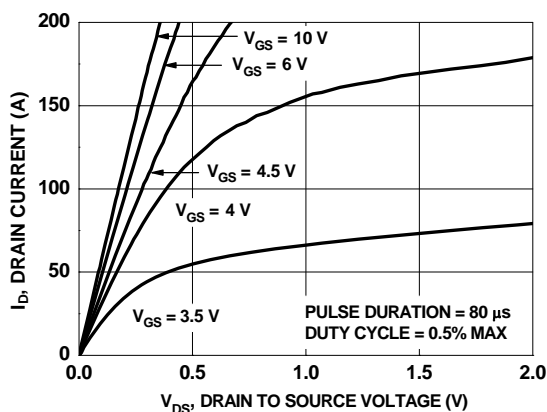


Figure 1. On Region Characteristics

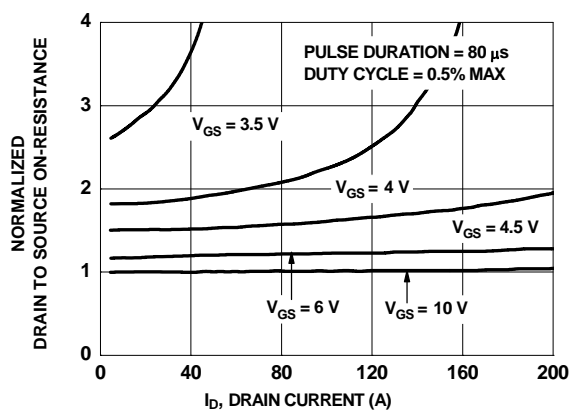


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

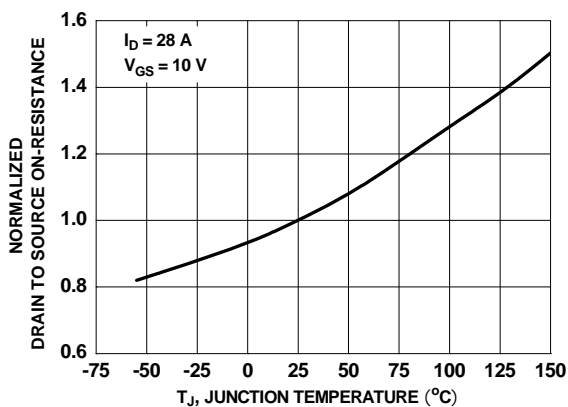


Figure 3. Normalized On Resistance vs Junction Temperature

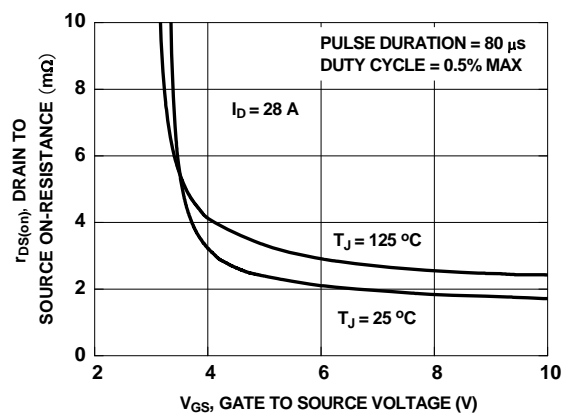


Figure 4. On-Resistance vs Gate to Source Voltage

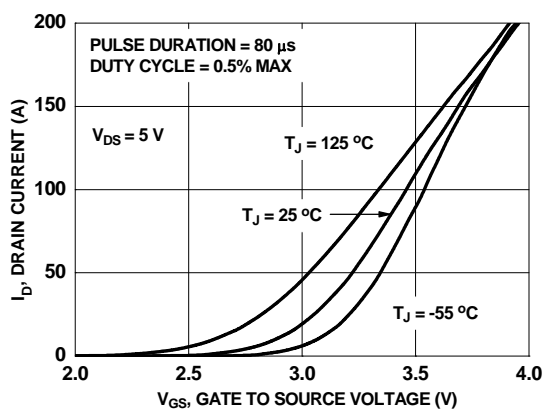


Figure 5. Transfer Characteristics

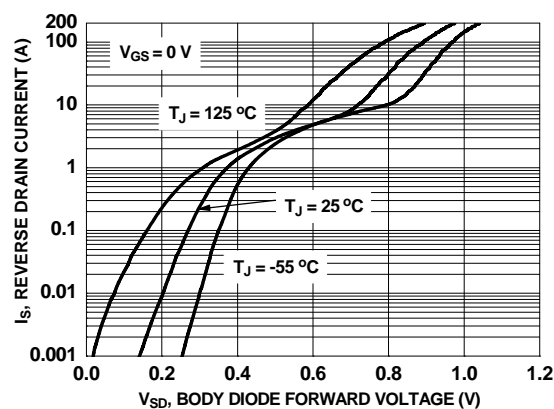


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

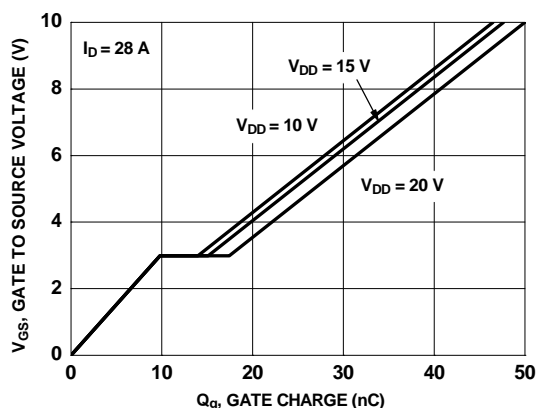


Figure 7. Gate Charge Characteristics

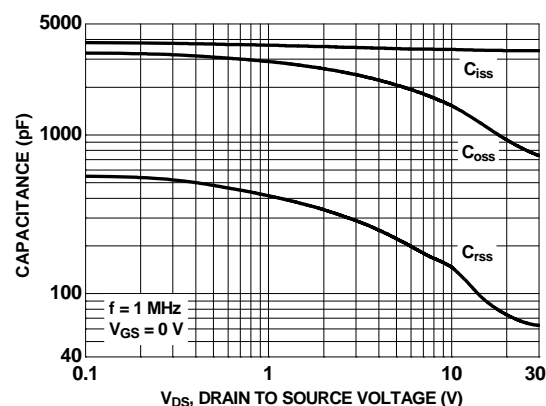


Figure 8. Capacitance vs Drain to Source Voltage

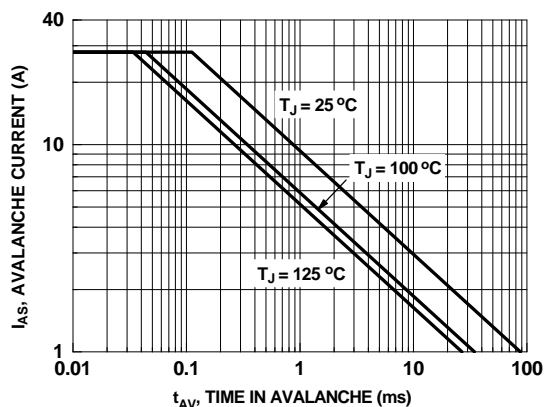


Figure 9. Unclamped Inductive Switching Capability

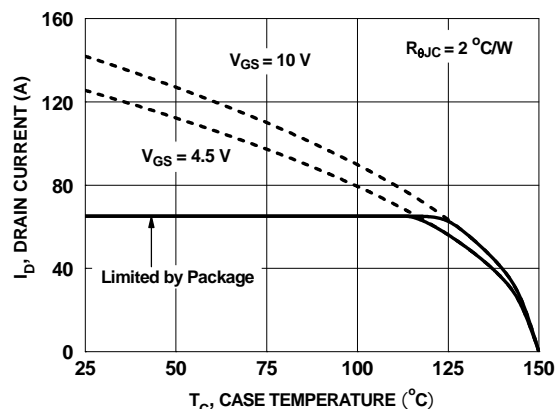


Figure 10. Maximum Continuous Drain Current vs Case Temperature

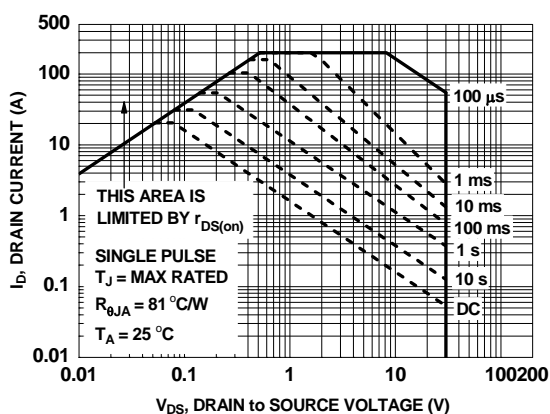


Figure 11. Forward Bias Safe Operating Area

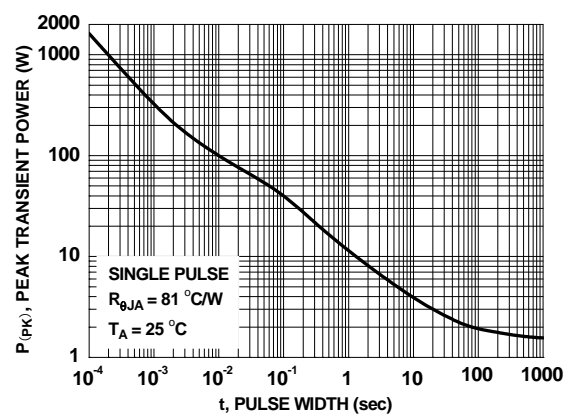


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

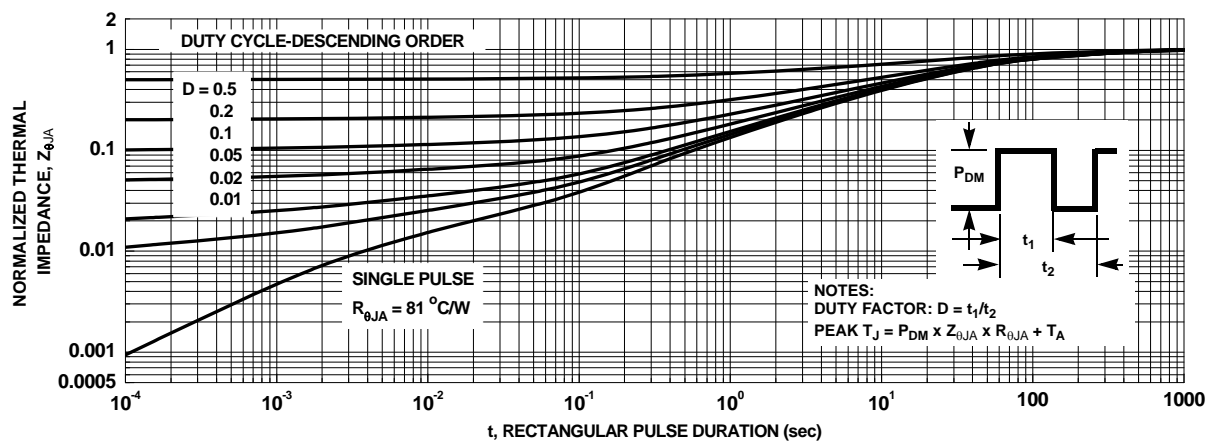


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky body diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS3008SDC.

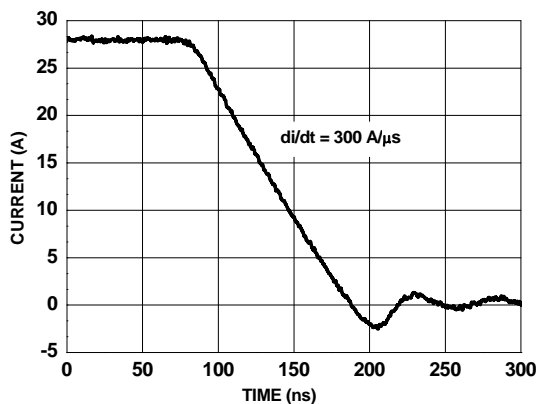


Figure 14. FDMS3008SDC SyncFET body diode reverse recovery characteristic

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

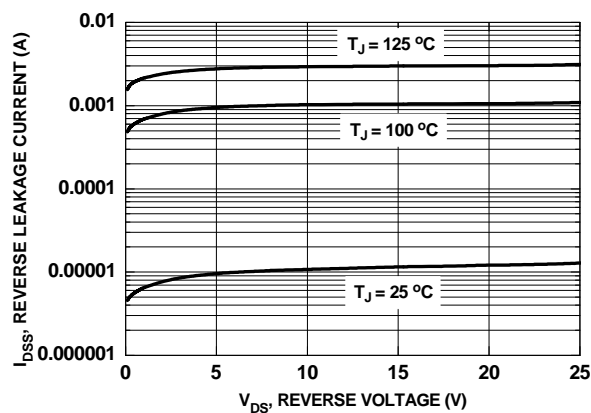


Figure 15. SyncFET body diode reverse leakage versus drain-source voltage

Dimensional Outline and Pad Layout

